优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

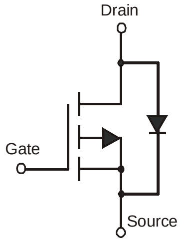
- P-Channel MOSFET
- Low On-Resistance
    - 150 mΩ @ V_{GS} = -4.5V
    - 200 mΩ @ V_{GS} = -2.5V
    - 240 mΩ @ V_{GS} = -1.8V
- Very Low Gate Threshold Voltage $V_{GS(th)} \leq 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Mechanical Data

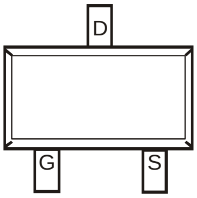
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)

SOT-323

Top View



Internal Schematic



Top View

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 1)	T_A = 25°C T_A = 70°C	I_D	-1.5 -1.0	A
Pulsed Drain Current		I_{DM}	-5	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:
1. Device mounted on FR-4 substrate PC board, 2oz. Copper, with minimum recommended pad layout.
2. No purposefully added lead.
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = 25°C T_J = 125°C	I_{DSS}	—	—	-1.0 -5.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.45	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	92	150	mΩ	V_{GS} = -4.5V, I_D = -2.0A
			134	200		V_{GS} = -2.5V, I_D = -1.5A
			180	240		V_{GS} = -1.8V, I_D = -0.5A
Forward Transconductance	g_{FS}	—	3.1	—	S	V_{DS} = -10V, I_D = -810mA
Diode Forward Voltage (Note 4)	V_{SD}	—	—	-0.9	V	V_{GS} = 0V, I_S = -0.5A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	320	—	pF	V_{DS} = -16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	80	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	60	—	pF	
Turn-On Delay Time	$t_{D(on)}$	—	12.5	—	ns	V_{DS} = -10V, V_{GS} = -4.5V, R_L = 10Ω, R_G = 1.0Ω
Turn-On Rise Time	t_r	—	10.3	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	46.5	—	ns	
Turn-Off Fall Time	t_f	—	22.2	—	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

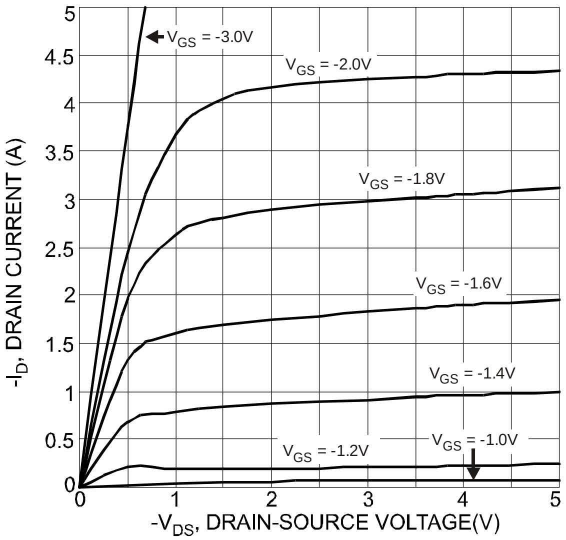


Fig.1 Typical Output Characteristics

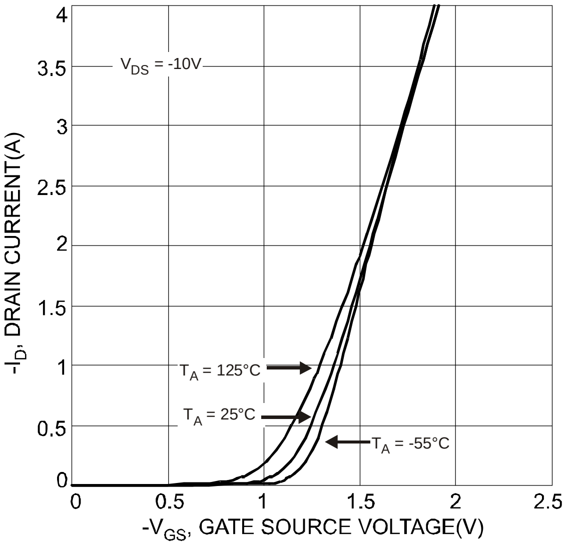


Fig. 2 Typical Transfer Characteristics

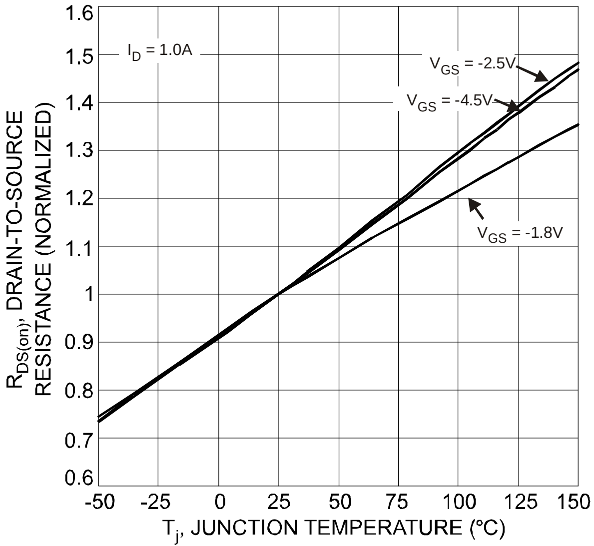


Fig. 3 On-Resistance Variation with Temperature

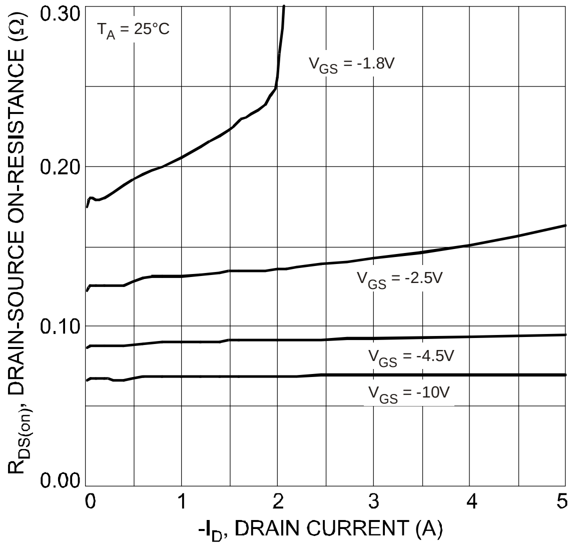


Fig. 4 On-Resistance vs Drain Current and Gate Voltage

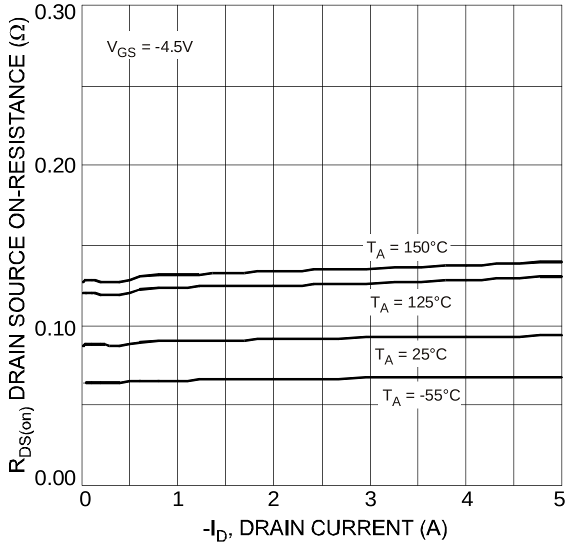


Fig. 5 Drain-Source On-Resistance
Vs. Drain Current and Temperature

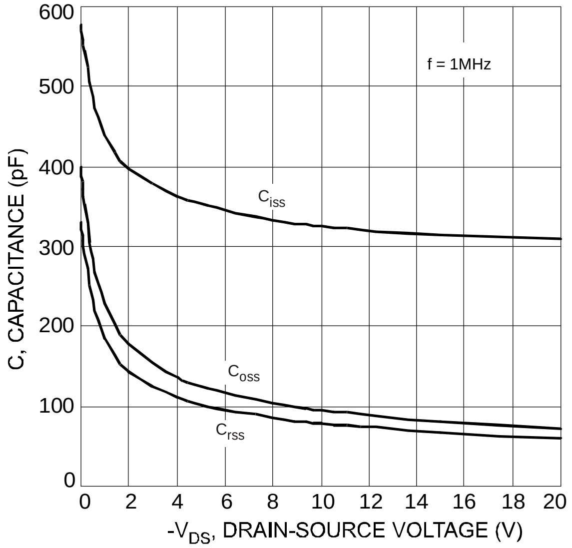


Fig. 6: Typical Capacitance

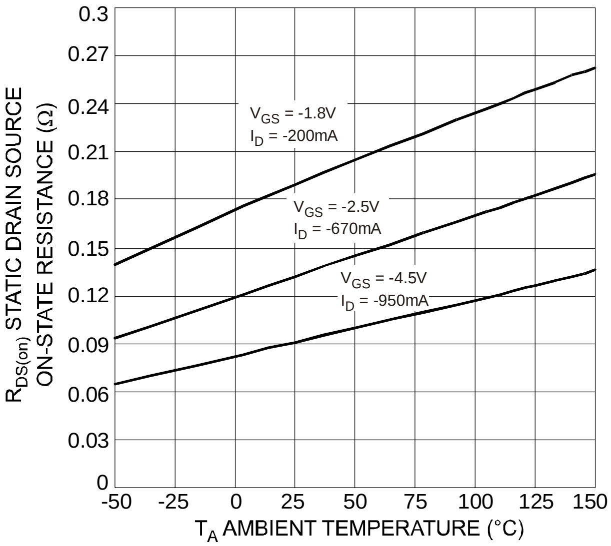


Fig. 7 Static Drain-Source On-State Resistance
vs Ambient Temperature

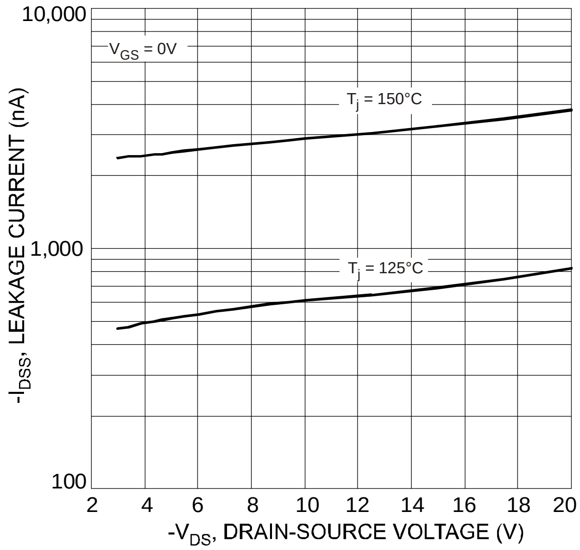


Fig. 8 Drain-Source Leakage Current vs Voltage

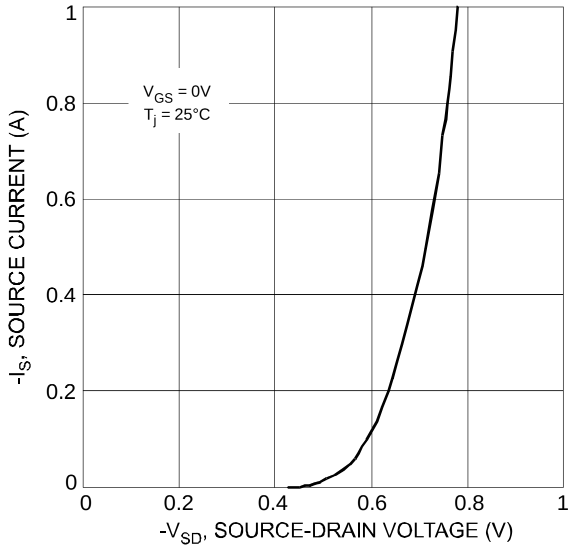
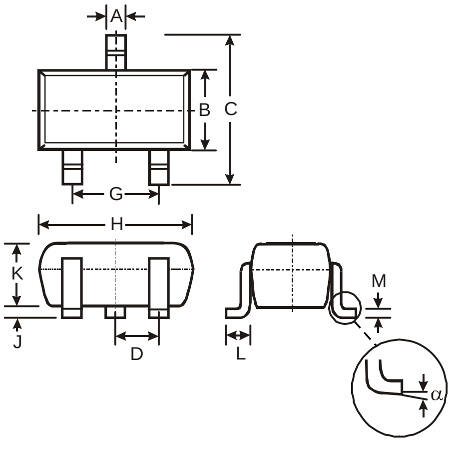


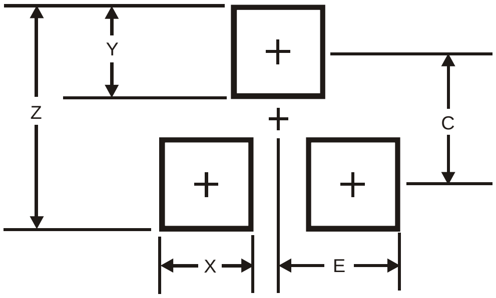
Fig. 9 Diode Forward Voltage vs. Current

Package Outline Dimensions



SOT-323			
Dim	**Min**	**Max**	**Typ**
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0